

Introduction

This application note describes the demonstration board of the DMOS dual full-bridge L6226Q designed for motor control applications. The board implements a typical application that can be used as a reference design to drive two-phase bipolar stepper motors with currents up to 1A DC, multiple DC motors and a wide range of inductive loads.

Thanks to the small footprint of the L6226Q (QFN 5 x 5 mm, 32-lead) the PCB is very compact (27 x 24.5 mm).

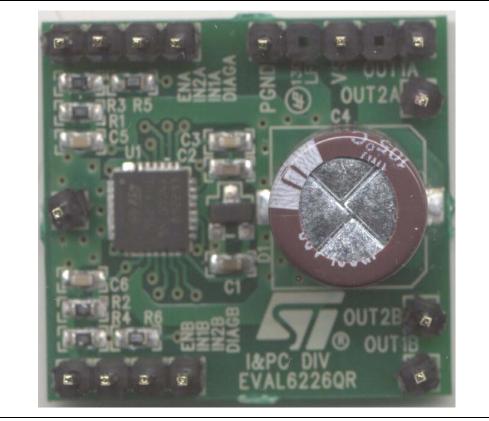


Figure 1. EVAL6226QR demonstration board

1 Demonstration board description

| Table 1. EVAL6226R pin connections | | | | |
|------------------------------------|-------------------|---|--|--|
| Name | Туре | Function | | |
| VS | Power supply | Bridge A and bridge B power supply | | |
| PGND | Ground | Power ground terminal | | |
| IN1A | Logic input | Bridge A logic input 1 | | |
| IN2A | Logic Input | Bridge A logic input 2 | | |
| ENA Logic input | | Bridge A enable (active high). When low, the power DMOSs of bridge A are switched OFF. | | |
| IN1B | Logic input | Bridge B logic input 1 | | |
| IN2B | Logic input | Bridge B logic input 2 | | |
| ENB | Logic input | Bridge B enable (active high). When low, the power DMOSs of bridge B are switched OFF. | | |
| DIAGA | Open drain output | Bridge A overcurrent detection and thermal protection pin. An internal open drain transistor pulls to GND when overcurrent on bridge A is detected or in case of thermal protection. | | |
| DIAGB | Open drain output | Bridge B overcurrent detection and thermal protection pin. An internal open drain transistor pulls to GND when overcurrent on bridge B is detected or in case of thermal protection. | | |
| SGND | Ground | Signal ground terminal | | |
| OUT1A | Power output | Bridge A output 1 | | |
| OUT2A | Power output | Bridge A output 2 | | |
| OUT1B | Power output | Bridge B output 1 | | |
| OUT2B Power output | | Bridge B output 2 | | |

Table 1. EVAL6226R pin connections

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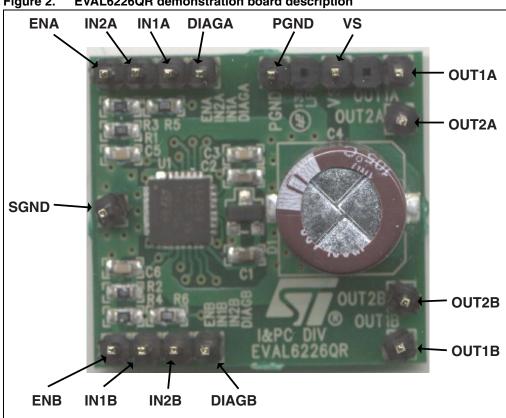


Figure 2. EVAL6226QR demonstration board description

The INx input pins drive the corresponding half-bridge. When low logic level is applied the low side MOS is switched on, whereas a high logic level turns on the high side MOS.

Pins ENA and ENB are used to implement overcurrent and thermal protection when connected respectively to the outputs DIAGA and DIAGB.

The output current detection thresholds are selected by the resistor connected between the IC dedicated pins and ground.

Table 2 summarizes the electrical specification of the application and Figure 3 shows the electrical schematic.

| Parameter | Value | | |
|---|---------------|--|--|
| Supply voltage range (VS) | 8 to 52 Vdc | | |
| RMS output current rating (OUTx) | up to 1.4 A | | |
| Switching frequency | up to 100 kHz | | |
| Input and enable voltage range | 0 to + 5 V | | |
| OCD pins voltage range | -0.3 to 10 V | | |
| Operating temperature range | -25 to +125°C | | |
| L6226Q thermal resistance junction to ambient | 42°C/W | | |
| | | | |

Table 2. EVAL6226QR electrical specification (recommended value)



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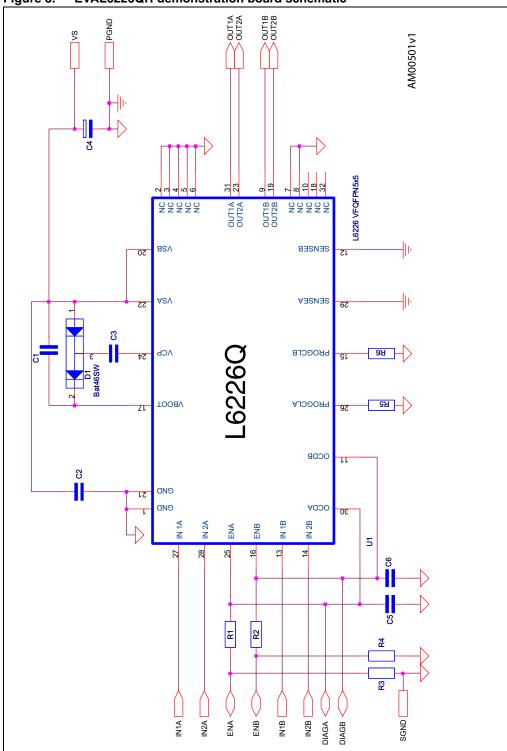


Figure 3. EVAL6226QR demonstration board schematic

| Part reference | Part value | Part description |
|----------------|------------------|-------------------------------|
| C1 | 220 nF/25 V | Capacitor |
| C2 | 220 nF/63 V | Capacitor |
| C3 | 10 nF/25 V | Capacitor |
| C4 | 100 μF/63 V | Capacitor |
| C5, C6 | 5.6 nF | Capacitor |
| D1 | BAT46SW | Diodes |
| R1, R2, R3, R4 | 100 kΩ 5% 0.25 W | Resistor |
| R5, R6 | 10 kΩ 1% 0.25 W | Resistor |
| R9, R10 | 0.4 kΩ 1 W | Resistor |
| U1 | L6226Q | Dual full-bridge in VFQFPN5x5 |

Table 3. EVAL6226QR part list

D1, C1 and C3 constitute a charge pump circuit, which generates the supply voltage for the high-side integrated MOSFETs. Due to voltage and current switching at relatively high frequency, these components are connected through short paths in order to minimize induced noise on other circuitries.

R1, R2 and C5, C6 are used by the overcurrent protection integrated circuitry (disable time t_{DISABLE} is about 200 µs and delay time t_{DELAY} about 1 µs using the values in *Table 3*).

R5 and R6 are used to set the output current detection threshold at about 1.1 A typical value. *Figure 4*, *Figure 5* and *Figure 6* show the placement of the components and the layout of the two layers of the EVAL6226QR reference design board. A GND area has been used to improve the IC power dissipation.

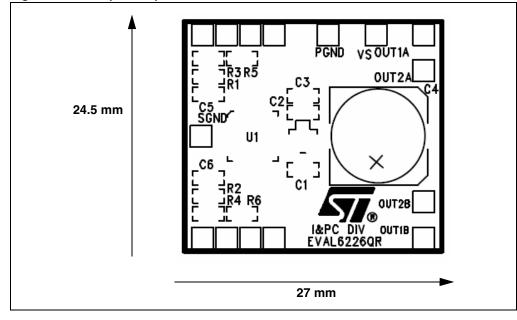


Figure 4. Component placement



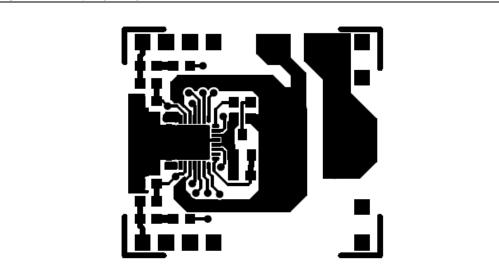
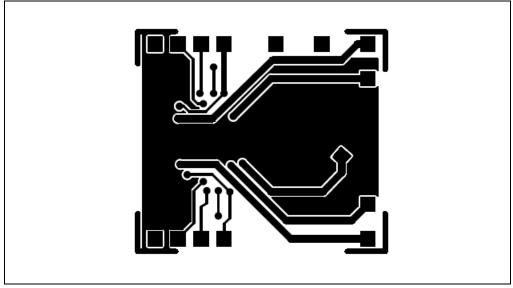


Figure 6. Bottom layer layout



2 Revision history

Table 4. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 06-Oct-2008 | 1 | Initial release |
| 28-Jan-2009 | 2 | Updated value in <i>Table 2: EVAL6226QR electrical specification</i> (recommended value) on page 3 |



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